



ULTRA HIGH DYNAMIC RANGE

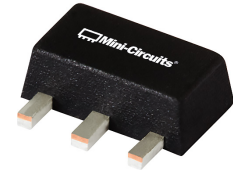
Monolithic Amplifier

PHA-1+

50Ω 0.05 to 6 GHz

THE BIG DEAL

- Ultra High IP3
- High Pout, P1dB 22 dBm typ. at 2 GHz, 5V
- Low noise figure, 2.2 dB @2 GHz, 5V
- Usable to 4.0V
- Broadband High Dynamic Range without External Matching Components
- May be used as a replacement to WJ AH1^{a,b}



Generic photo used for illustration purposes only
CASE STYLE: DF782

+RoHS Compliant
The +Suffix identifies RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications

APPLICATIONS

- Base station infrastructure
- Portable Wireless
- CATV & DBS
- MMDS & Wireless LAN
- LTE

LTE Performance

TD-SCDMA Performance

FREE X-PARAMETERS*

PRODUCT OVERVIEW

PHA-1+ (RoHS compliant) is an advanced wideband amplifier fabricated using E-PHEMT technology and offers extremely high dynamic range over a broad frequency range and with low noise figure. In addition, the PHA-1+, unlike competitive models, has good input and output return loss over a broad frequency range without the need for external matching components and has demonstrated excellent reliability. It has repeatable performance from lot to lot and is enclosed in a SOT-89 package for very good thermal performance.

KEY FEATURES

Feature	Advantages
Broad Band: 0.05 to 6.0 GHz	Broadband covering primary wireless communications bands: Cellular, PCS, LTE, WiMAX
Extremely High IP3 Versus DC power Consumption 42 dBm typical at 2 GHz	The PHA-1+ matches industry leading IP3 performance relative to device size and power consumption. The combination of the design and E-PHEMT Structure provides enhanced linearity over a broad frequency range as evidence in the IP3 being typically 20 dB above the P 1dB point. This feature makes this amplifier ideal for use in: <ul style="list-style-type: none"> • Driver amplifiers for complex waveform up converter paths • Drivers in linearized transmit systems • Secondary amplifiers in ultra High Dynamic range receivers
No External Matching Components Required	Unlike competing products, Mini-Circuits PHA-1+ provides Input and Output Return Loss of 14-21 dB up to 4 GHz without the need for any external matching components
Low Noise Figure: 2.3dB typ. up to 4 GHz 3.5dB typ. up to 6 GHz	A unique feature of the PHA-1+ which separates this design from all competitors is the low noise figure performance in combination with the high dynamic range.

a. Suitability for model replacement within a particular system must be determined by and is solely the responsibility of the customer based on, among other things, electrical performance criteria, stimulus conditions, application, compatibility with other components and environmental conditions and stresses.
b. The WJ AH1 part number is used for identification and comparison purposes only.

* X-parameters is a registered trademark of Agilent Technologies, Inc. The X-parameters format and underlying equations are open and documented. For more information, refer to X-parameters Open Documentation, Trademark Usage & Partnerships

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ECO-010314
PHA-1+
MCL NY
211026





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PHA-1+

ELECTRICAL SPECIFICATIONS AT 25°C, UNLESS NOTED

Parameter	Condition (GHz)	Vd=5.0V ⁽¹⁾			Vd=4.5V ⁽²⁾	Vd=4.0V ⁽²⁾	Units
		Min.	Typ.	Max.	Typ.	Typ.	
Frequency range		0.05		6.0	0.05-6.0	0.05-6.0	GHz
Gain	0.05	15.4	17.2	19.4	17.5	17.3	dB
	0.8	14.1	15.7	17.3	15.5	15.2	
	2.0	—	13.5	—	13.4	13.1	
	3.0	—	11.8	—	11.8	11.4	
	4.0	9.6	10.7	12.3	10.7	10.4	
	6.0	—	9.7	—	9.6	9.2	
Input Return Loss	0.05	—	11.7	—	10.7	10.6	dB
	0.8	13.0	17.0	—	16.5	16.1	
	2.0	—	11.3	—	11.7	11.4	
	3.0	—	10.2	—	10.4	10.1	
	4.0	—	10.2	—	9.7	9.5	
	6.0	—	8.6	—	7.3	7.3	
Output Return Loss	0.05	—	14.5	—	13.7	13.5	dB
	0.8	13.0	20.8	—	19.5	18.3	
	2.0	—	17.1	—	16.1	14.7	
	3.0	—	15.3	—	14.1	13.4	
	4.0	—	13.8	—	12.8	12.2	
	6.0	—	11.0	—	10.2	9.7	
Reverse Isolation	2.0		19.9		19.3	18.9	dB
Output Power @1 dB compression	0.05	20.0	22.2	—	21.5	20.0	dBm
	0.8	20.0	22.6	—	21.3	19.9	
	2.0	20.0	22.4	—	21.4	19.9	
	3.0	—	22.7	—	21.6	20.1	
	4.0	—	22.7	—	21.5	20.1	
	6.0	—	21.6	—	20.3	19.2	
Output IP3	0.05	—	41.4	—	36.8	34.4	dBm
	0.8	37.0	41.1	—	40.0	36.3	
	2.0	—	42.0	—	37.1	34.0	
	3.0	—	42.3	—	36.3	33.3	
	4.0	—	40.8	—	35.8	32.7	
	6.0	—	38.8	—	33.9	31.2	
Noise Figure	0.05	—	1.7	—	1.9	1.8	dB
	1.0	—	1.9	—	2.3	2.1	
	2.0	—	2.2	—	2.4	2.2	
	3.0	—	2.3	—	2.5	2.5	
	4.0	—	2.7	—	3.0	2.9	
	6.0	—	3.5	—	3.7	3.6	
Device Operating Voltage		4.8	5.0	5.2	4.5	4.0	V
Device Operating Current		110	146	180	119	95	mA
Device Current Variation vs. Temperature ⁽³⁾			-12		68	67	μA/°C
Device Current Variation vs Voltage			0.054		0.052	0.052	mA/mV
Thermal Resistance, junction-to-ground lead			60		60	60	°C/W

(1) Measured on Mini-Circuits Characterization test board TB-313. See Characterization Test Circuit (Fig. 1)

(2) Measured on Mini-Circuits test fixture 90-6-20-26 characterization Circuit (Fig.1), except replace TB-313 with 90-6-20-26

(3) (Current at 85°C – Current at -45°C)/130





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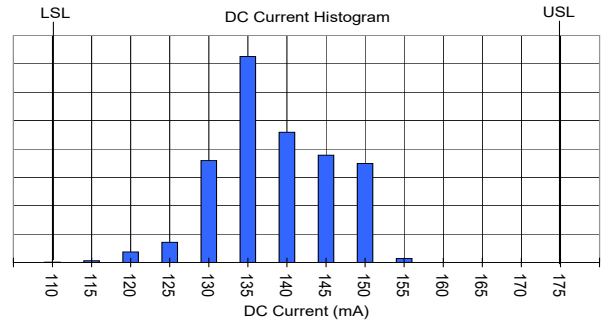
Monolithic Amplifier

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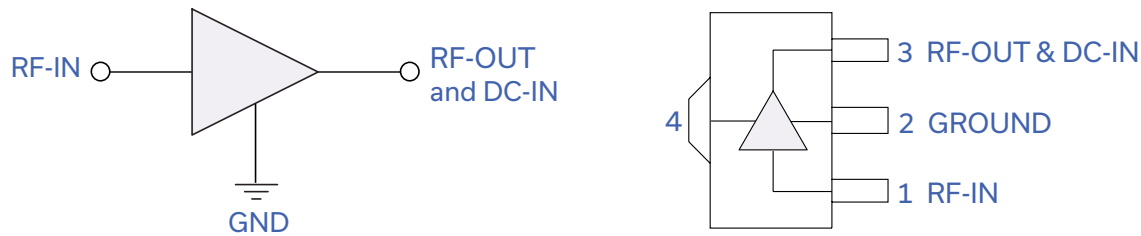
MAXIMUM RATINGS

Parameter	Ratings
Operating Temperature (ground lead)	-40°C to 85°C
Storage Temperature	-65°C to 150°C
Operating Current at 5V	210 mA
Power Dissipation	1 W
Input Power (CW)	24 dBm
DC Voltage on Pin 3	6 V

Permanent damage may occur if any of these limits are exceeded. Electrical maximum ratings are not intended for continuous normal operation.



SIMPLIFIED SCHEMATIC AND PIN DESCRIPTION



Function	Pin Number	Description
RF IN	1	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.
RF-OUT and DC-IN	3	RF output and bias pin. DC voltage is present on this pin; therefore a DC blocking capacitor is necessary for proper operation. An RF choke is needed to feed DC bias without loss of RF signal due to the bias connection, as shown in "Recommended Application Circuit", Fig. 2
GND	2,4	Connections to ground. Use via holes as shown in "Suggested Layout for PCB Design" to reduce ground path inductance for best performance.

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CHARACTERIZATION TEST CIRCUIT

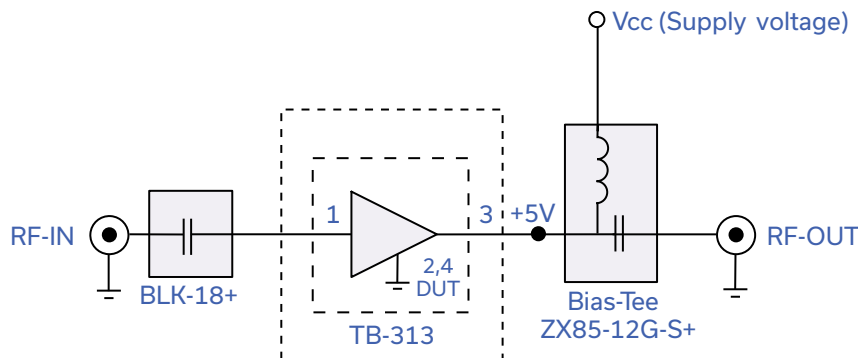


Fig 1. Block Diagram of Test Circuit used for characterization. (DUT soldered on Mini-Circuits Characterization test board TB-313)

Gain, Return loss, Output power at 1dB compression (P1 dB) , output IP3 (OIP3) and noise figure measured using Agilent's N5242A PNA-X microwave network analyzer.

Conditions:

1. Gain and Return loss: Pin= -25dBm
2. Output IP3 (OIP3): Two tones, spaced 1 MHz apart, 5 dBm/ tone at output.





RECOMMENDED APPLICATION CIRCUIT

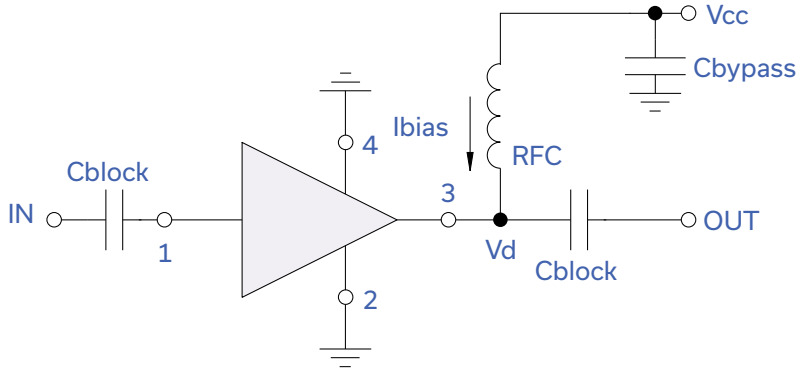
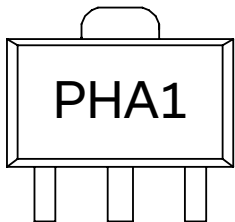


Fig 2. Test Board includes case, connectors, and components soldered to PCB

PRODUCT MARKING



Marking may contain other features or characters for internal lot control